

AMENDMENTS TO THE ABSTRACT:

Please replace the Abstract originally appearing on page 17 of the application with the following rewritten paragraph:

ABSTRACT OF THE DISCLOSURE

Silicide interfaces for integrated circuits, thin film devices, and back-end integrated circuit testing devices are formed using a barrier layer, such as titanium nitride, disposed over a porous, thin dielectric layer which is disposed between a silicon-containing substrate and a silicidable material which is deposited to form the silicide interfaces for such devices. The barrier layer prevents the formation of a silicide material within imperfections or voids which form passages through the thin dielectric layer when the device is subjected to a high temperature anneal to form the silicide contact from the reaction of the silicidable material and the ~~silicon-~~silicon-containing substrate.